QUAD BILATERAL SWITCHES

FEATURES

- Low "ON" resistance:
  160 Ω (typ.) at $V_{CC} - V_{EE} = 4.5$ V
  120 Ω (typ.) at $V_{CC} - V_{EE} = 6.0$ V
  80 Ω (typ.) at $V_{CC} - V_{EE} = 9.0$ V
- Logic level translation: to enable 5 V logic to communicate with ± 5 V analog signals
- Typical "break before make" built in
- Output capability: non-standard
- I_{CC} category: MSI

GENERAL DESCRIPTION

The 74HC/HCT4316 are high-speed Si-gate CMOS devices.
They are specified in compliance with JEDEC standard no. 7A.

The 74HC/HCT4316 have four independent analog switches.
Each switch has two input/output terminals (nY, nZ) and an active HIGH select input (nS). When the enable input ($\overline{E}$) is HIGH, all four analog switches are turned off.

Current through a switch will not cause additional V_{CC} current provided the voltage at the terminals of the switch is maintained within the supply voltage range; $V_{CC} \gg (V_Y, V_Z) \gg V_{EE}$.
Inputs nY and nZ are electrically equivalent terminals.

V_{CC} and GND are the supply voltage pins for the digital control inputs ($\overline{E}$ and nS).
The V_{CC} to GND ranges are 2.0 to 10.0 V for HC and 4.5 to 5.5 V for HCT.
The analog inputs/outputs (nY and nZ) can swing between V_{CC} as a positive limit and V_{EE} as a negative limit.
$V_{CC} - V_{EE}$ may not exceed 10.0 V.

See the "4016" for the version without logic level translation.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL		UNIT
			HC	HCT	
t_{PZH}	turn "ON" time $\overline{E}$ to V_{os} nS to V_{os}	$C_L = 15$ pF $R_L = 1$ kΩ $V_{CC} = 5$ V	 19 16	 19 17	 ns ns
t_{PZL}	turn "ON" time $\overline{E}$ to V_{os} nS to V_{os}		 19 16	 24 21	 ns ns
$t_{PHZ}/$ t_{PLZ}	turn "OFF" time $\overline{E}$ to V_{os} nS to V_{os}		 20 16	 21 19	 ns ns
C_I	input capacitance		3.5	3.5	pF
C_{PD}	power dissipation capacitance per switch	notes 1 and 2	13	14	pF
C_S	max. switch capacitance		5	5	pF

$V_{EE} = GND = 0$ V; $T_{amb} = 25$ °C; $t_r = t_f = 6$ ns

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
   $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma\{(C_L + C_S) \times V_{CC}^2 \times f_o\}$ where:
   f_i = input frequency in MHz
   f_o = output frequency in MHz
   $\Sigma\{(C_L + C_S) \times V_{CC}^2 \times f_o\}$ = sum of outputs
   C_L = output load capacitance in pF
   C_S = max. switch capacitance in pF
   V_{CC} = supply voltage in V
2. For HC the condition is V_I = GND to V_{CC}
   For HCT the condition is V_I = GND to $V_{CC} - 1.5$ V

PACKAGE OUTLINES

16-lead DIL; plastic (SOT38Z).
16-lead mini-pack; plastic (SO16; SOT109A).

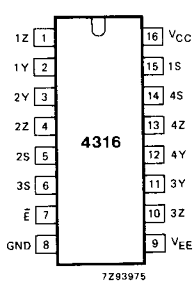


Fig. 1 Pin configuration.

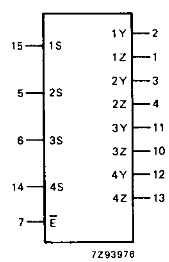


Fig. 2 Logic symbol.

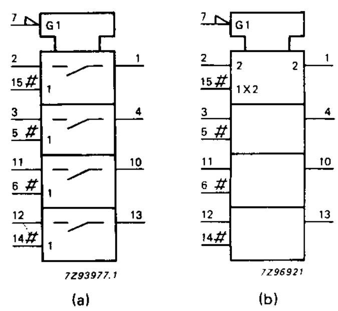


Fig. 3 IEC logic symbol.

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
1, 4, 10, 13	1Z to 4Z	independent inputs/outputs
2, 3, 11, 12	1Y to 4Y	independent inputs/outputs
7	$\bar{E}$	enable input (active LOW)
8	GND	ground (0 V)
9	V_{EE}	negative supply voltage
15, 5, 6, 14	1S to 4S	select inputs (active HIGH)
16	V_{CC}	positive supply voltage

FUNCTION TABLE

INPUTS		SWITCH
$\bar{E}$	nS	
L	L	off
L	H	on
H	X	off

H = HIGH voltage level
L = LOW voltage level
X = don't care

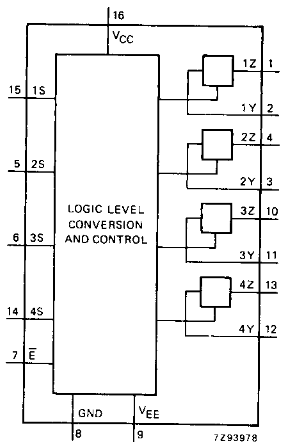


Fig. 4 Functional diagram.

APPLICATIONS

- **Signal gating**
- **Modulation**
- **Demodulation**
- **Chopper**

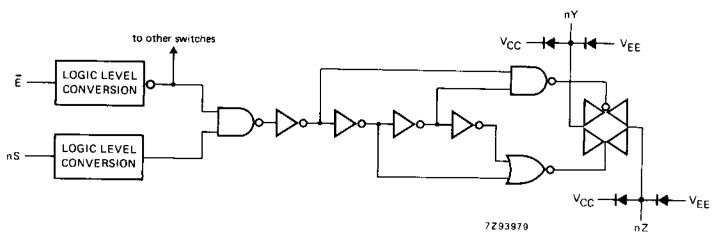


Fig. 5 Schematic diagram (one switch).

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Voltages are referenced to V_{EE} = GND (ground = 0 V)

SYMBOL	PARAMETER	MIN.	MAX.	UNIT	CONDITIONS
V_{CC}	DC supply voltage	−0.5	+11.0	V	
$\pm I_{IK}$	DC digital input diode current		20	mA	for $V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V
$\pm I_{SK}$	DC switch diode current		20	mA	for $V_S < -0.5$ V or $V_S > V_{CC} + 0.5$ V
$\pm I_S$	DC switch current		25	mA	for -0.5 V $< V_S < V_{CC} + 0.5$ V
$\pm I_{EE}$	DC V_{EE} current		20	mA	
$\pm I_{CC}$; $\pm I_{GND}$	DC V_{CC} or GND current		50	mA	
T_{stg}	storage temperature range	−65	+150	°C	
P_{tot}	power dissipation per package				for temperature range: −40 to +125 °C 74HC/HCT
	plastic DIL		750	mW	above +70 °C: derate linearly with 12 mW/K
	plastic mini-pack (SO)		500	mW	above +70 °C: derate linearly with 8 mW/K
P_S	power dissipation per switch		100	mW	

Note to ratings

To avoid drawing V_{CC} current out of terminal Z, when switch current flows in terminals Y_n, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no V_{CC} current will flow out of terminal Y_n. In this case there is no limit for the voltage drop across the switch, but the voltages at Y_n and Z may not exceed V_{CC} or V_{EE}.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	74HC			74HCT			UNIT	CONDITIONS
		min.	typ.	max.	min.	typ.	max.		
V_{CC}	DC supply voltage V_{CC}–GND	2.0	5.0	10.0	4.5	5.0	5.5	V	see Figs 6 and 7
V_{CC}	DC supply voltage V_{CC}–V_{EE}	2.0	5.0	10.0	2.0	5.0	10.0	V	see Figs 6 and 7
V_I	DC input voltage range	GND		V_{CC}	GND		V_{CC}	V	
V_S	DC switch voltage range	V_{EE}		V_{CC}	V_{EE}		V_{CC}	V	
T_{amb}	operating ambient temperature range	−40		+85	−40		+85	°C	see DC and AC CHARACTERISTICS
T_{amb}	operating ambient temperature range	−40		+125	−40		+125	°C	
t_r, t_f	input rise and fall times		6.0	1000 500 400 250		6.0	500	ns	V_{CC} = 2.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V V_{CC} = 10.0 V

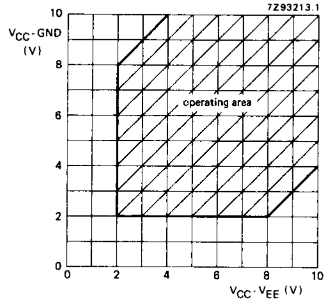


Fig. 6 Guaranteed operating area as a function of the supply voltages for 74HC4316.

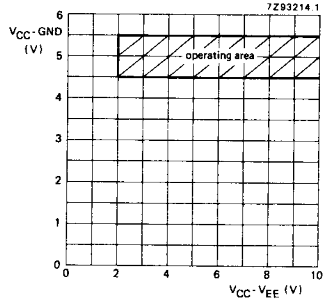


Fig. 7 Guaranteed operating area as a function of the supply voltages for 74HCT4316.

DC CHARACTERISTICS FOR 74HC/HCT

For 74HC: V_{CC} – GND or V_{CC} – V_{EE} = 2.0, 4.5, 6.0 and 9.0 V
For 74HCT: V_{CC} – GND = 4.5 and 5.5 V; V_{CC} – V_{EE} = 2.0, 4.5, 6.0 and 9.0 V

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS				
		74HC/HCT								V_{CC} V	V_{EE} V	I_S μA	V_{is}	V_I
		+25			−40 to +85		−40 to +125							
		min.	typ.	max.	min.	max.	min.	max.						
R_{ON}	ON resistance (peak)		– 160 120 85	– 320 240 170		– 400 300 215		– 480 360 255	Ω Ω Ω Ω	2.0 4.5 6.0 4.5	0 0 0 −4.5	100 1000 1000 1000	V_{CC} to V_{EE}	V_{IH} or V_{IL}
R_{ON}	ON resistance (rail)		160 80 70 60	– 160 140 120		– 200 175 150		– 240 210 180	Ω Ω Ω Ω	2.0 4.5 6.0 4.5	0 0 0 −4.5	100 1000 1000 1000	V_{EE}	V_{IH} or V_{IL}
R_{ON}	ON resistance (rail)		170 90 80 65	– 180 160 135		– 225 200 170		– 270 240 205	Ω Ω Ω Ω	2.0 4.5 6.0 4.5	0 0 0 −4.5	100 1000 1000 1000	V_{CC}	V_{IH} or V_{IL}
ΔR_{ON}	maximum ΔON resistance between any two channels		– 16 9 6						Ω Ω Ω Ω	2.0 4.5 6.0 4.5	0 0 0 −4.5		V_{CC} to V_{EE}	V_{IH} or V_{IL}

Notes to DC characteristics

1. At supply voltages (V_{CC} – V_{EE}) approaching 2.0 V the analog switch ON-resistance becomes extremely non-linear. Therefore it is recommended that these devices be used to transmit digital signals only, when using these supply voltages.
2. For test circuit measuring R_{ON} see Fig. 8.

DC CHARACTERISTICS FOR 74HC

Voltages are referenced to GND (ground = 0 V)

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS			
		74HC								V_{CC} V	V_{EE} V	V_I	OTHER
		+25			−40 to +85		−40 to +125						
		min.	typ.	max.	min.	max.	min.	max.					
V_{IH}	HIGH level input voltage	1.5 3.15 4.2 6.3	1.2 2.4 3.2 4.3		1.5 3.15 4.2 6.3		1.5 3.15 4.2 6.3		V	2.0 4.5 6.0 9.0			
V_{IL}	LOW level input voltage		0.8 2.1 2.8 4.3	0.5 1.35 1.8 2.7		0.5 1.35 1.8 2.7		0.5 1.35 1.8 2.7	V	2.0 4.5 6.0 9.0			
$\pm I_I$	input leakage current			0.1 0.2		1.0 2.0		1.0 2.0	μA	6.0 10.0	0 0	V_{CC} or GND	
$\pm I_S$	analog switch OFF-state current			0.1		1.0		1.0	μA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ (see Fig. 10)
$\pm I_S$	analog switch ON-state current			0.1		1.0		1.0	μA	10.0	0	V_{IH} or V_{IL}	$\lvert V_S \rvert = V_{CC} - V_{EE}$ (see Fig. 11)
I_{CC}	quiescent supply current			8.0 16.0		80.0 160.0		160.0 320.0	μA	6.0 10.0	0 0	V_{CC} or GND	$V_{is} = V_{EE}$ or V_{CC}; $V_{os} = V_{CC}$ or V_{EE}

AC CHARACTERISTICS FOR 74HC

GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF

SYMBOL	PARAMETER	T_{amb} (°C) 74HC +25 min.	+25 typ.	+25 max.	−40 to +85 min.	−40 to +85 max.	−40 to +125 min.	−40 to +125 max.	UNIT	TEST CONDITIONS V_{CC} V	V_{EE} V	OTHER
t_{PHL}/ t_{PLH}	propagation delay V_{is} to V_{os}		17 6 5 4	60 12 10 8		75 15 13 10		90 18 15 12	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	$R_L = \infty$; $C_L = 50$ pF (see Fig. 18)
t_{PZH}/ t_{PZL}	turn "ON" time $\overline{E}$ to V_{os}		61 22 18 19	205 41 35 37		255 51 43 47		310 62 53 56	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)
t_{PZH}/ t_{PZL}	turn "ON" time nS to V_{os}		52 19 15 17	175 35 30 34		220 44 37 43		265 53 45 51	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)
t_{PHZ}/ t_{PLZ}	turn "OFF" time $\overline{E}$ to V_{os}		63 23 18 21	220 44 37 39		275 55 47 49		330 66 56 59	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)
t_{PHZ}/ t_{PLZ}	turn "OFF" time nS to V_{os}		55 20 16 18	175 35 30 36		220 44 37 45		265 53 45 54	ns	2.0 4.5 6.0 4.5	0 0 0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)

DC CHARACTERISTICS FOR 74HCT

Voltages are referenced to GND (ground = 0)

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS			
		74HCT								V_{CC} V	V_{EE} V	V_I	OTHER
		+25			−40 to +85		−40 to +125						
		min.	typ.	max.	min.	max.	min.	max.					
V_{IH}	HIGH level input voltage	2.0	1.6		2.0		2.0		V	4.5 to 5.5			
V_{IL}	LOW level input voltage		1.2	0.8		0.8		0.8	V	4.5 to 5.5			
$\pm I_I$	input leakage current			0.1		1.0		1.0	μA	5.5	0	V_{CC} or GND	
$\pm I_S$	analog switch OFF-state current			0.1		1.0		1.0	μA	10.0	0	V_{IH} or V_{IL}	$\|V_S\| = V_{CC} - V_{EE}$ (see Fig. 10)
$\pm I_S$	analog switch ON-state current			0.1		1.0		1.0	μA	10.0	0	V_{IH} or V_{IL}	$\|V_S\| = V_{CC} - V_{EE}$ (see Fig. 11)
I_{CC}	quiescent supply current			8.0 16.0		80.0 160.0		160.0 320.0	μA	5.5 5.0	0 −5.0	V_{CC} or GND	$V_{is} = V_{EE}$ or V_{CC}; $V_{os} = V_{CC}$ or V_{EE}
ΔI_{CC}	additional quiescent supply current per input pin for unit load coefficient is 1 (note 1)		100	360		450		490	μA	4.5 to 5.5	0	V_{CC} −2.1V	other inputs at V_{CC} or GND

Note to HCT types

1. The value of additional quiescent supply current (ΔI_{CC}) for a unit load of 1 is given here.
   To determine ΔI_{CC} per input, multiply this value by the unit load coefficient shown in the table below.

INPUT	UNIT LOAD COEFFICIENT
nS	0.50
$\overline{E}$	0.50

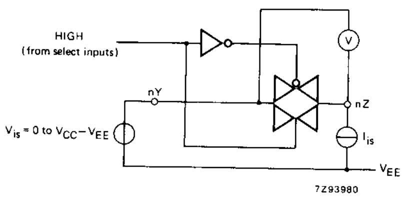


Fig. 8 Test circuit for measuring R_{ON}.

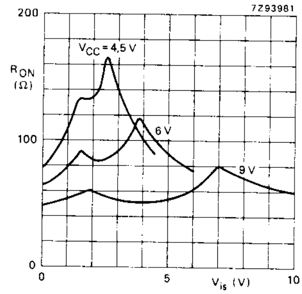


Fig. 9 Typical R_{ON} as a function of input voltage V_{is} for V_{is} = 0 to $V_{CC} - V_{EE}$.

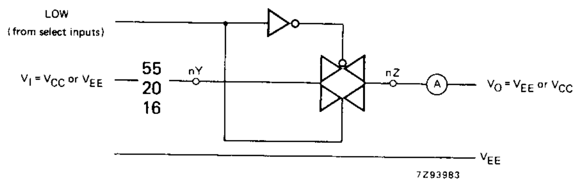


Fig. 10 Test circuit for measuring OFF-state current.

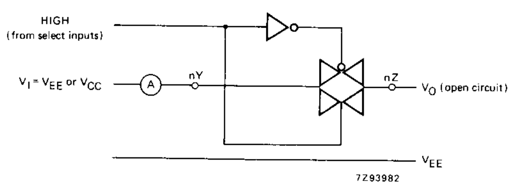


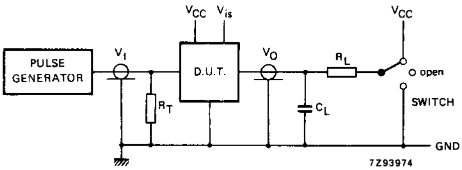
Fig. 11 Test circuit for measuring ON-state current.

AC CHARACTERISTICS FOR 74HCT

GND = 0 V; $t_r = t_f = 6$ ns; $C_L = 50$ pF

SYMBOL	PARAMETER	T_{amb} (°C)							UNIT	TEST CONDITIONS		
		74HCT								V_{CC} V	V_{EE} V	OTHER
		+25			−40 to +85		−40 to +125					
		min.	typ.	max.	min.	max.	min.	max.				
t_{PHL}/ t_{PLH}	propagation delay V_{is} to V_{os}		6 4	12 8		15 10		18 12	ns	4.5 4.5	0 −4.5	$R_L = \infty$; $C_L = 50$ pF (see Fig. 18)
t_{PZH}	turn "ON" time $\overline{E}$ to V_{os}		22 21	44 42		55 53		66 63	ns	4.5 4.5	0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)
t_{PZL}	turn "ON" time $\overline{E}$ to V_{os}		28 21	56 42		70 53		84 63	ns	4.5 4.5	0 −4.5	
t_{PZH}	turn "ON" time nS to V_{os}		20 17	40 34		53 43		60 51	ns	4.5 4.5	0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)
t_{PZL}	turn "ON" time nS to V_{os}		25 17	50 34		63 43		75 51	ns	4.5 4.5	0 −4.5	
t_{PHZ}/ t_{PLZ}	turn "OFF" time $\overline{E}$ to V_{os}		25 23	50 46		63 58		75 69	ns	4.5 4.5	0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)
t_{PHZ}/ t_{PLZ}	turn "OFF" time nS to V_{os}		22 20	44 40		55 50		66 60	ns	4.5 4.5	0 −4.5	$R_L = 1$ kΩ; $C_L = 50$ pF (see Figs 19, 20 and 21)

TEST CIRCUIT AND WAVEFORMS



Conditions

TEST	SWITCH	V_{is}
t_{PZH}	GND	V_{CC}
t_{PZL}	V_{CC}	GND
t_{PHZ}	GND	V_{CC}
t_{PLZ}	V_{CC}	GND
others	open	pulse

Fig. 18 Test circuit for measuring AC performance.

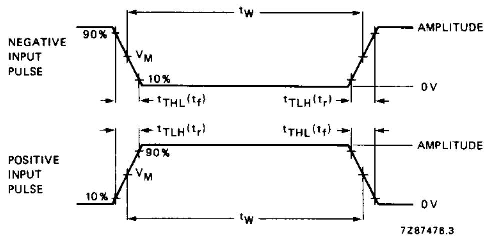


Fig. 19 Input pulse definitions.

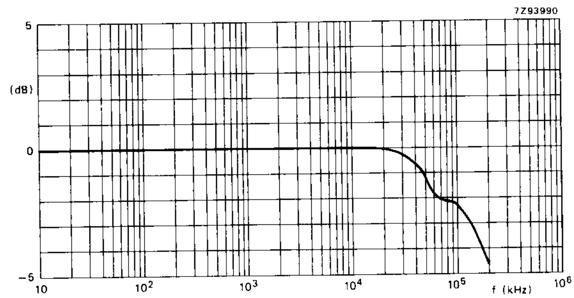
Definitions for Figs 18 and 19:

C_L = load capacitance including jig and probe capacitance (see AC CHARACTERISTICS for values).

R_T = termination resistance should be equal to the output impedance Z_O of the pulse generator.

t_r = t_f = 6 ns, when measuring f_{max}, there is no constraint on t_r, t_f with 50% duty factor.

FAMILY	AMPLITUDE	V_M	t_r; t_f	
			f_{max}; PULSE WIDTH	OTHER
74HC	V_{CC}	50%	< 2 ns	6 ns
74HCT	3.0 V	1.3 V	< 2 ns	6 ns



Note to Figs 12 and 13

Test conditions:
V_{CC} = 4.5 V; GND = 0 V; V_{EE} = −4.5 V;
R_L = 50 Ω; R_{source} = 1 kΩ.

Fig. 13 Typical frequency response.

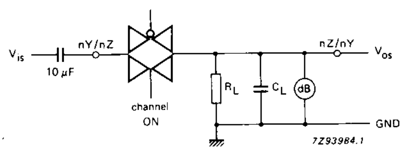


Fig. 14 Test circuit for measuring sine-wave distortion and minimum frequency response.

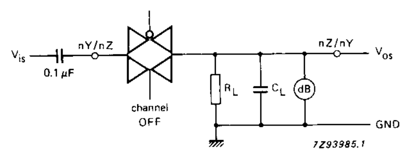
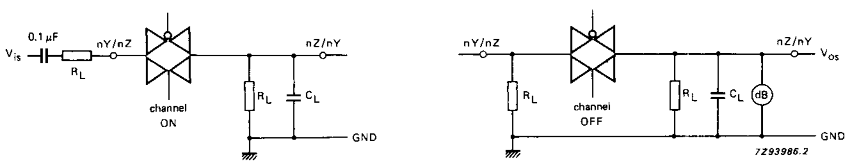


Fig. 15 Test circuit for measuring switch "OFF" signal feed-through.



(a)

(b)

Fig. 16 Test circuit for measuring crosstalk between any two switches.
(a) channel ON condition; (b) channel OFF condition.

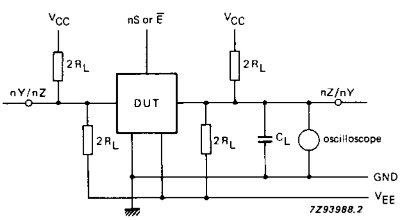
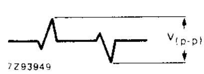


Fig. 17 Test circuit for measuring crosstalk between control and any switch.

Note to Fig. 17

The crosstalk is defined as follows (oscilloscope output):



AC WAVEFORMS

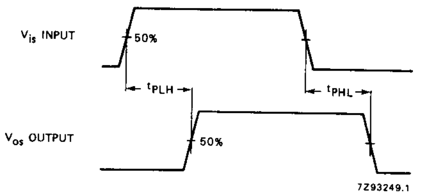


Fig. 18 Waveforms showing the input (V_{is}) to output (V_{OS}) propagation delays.

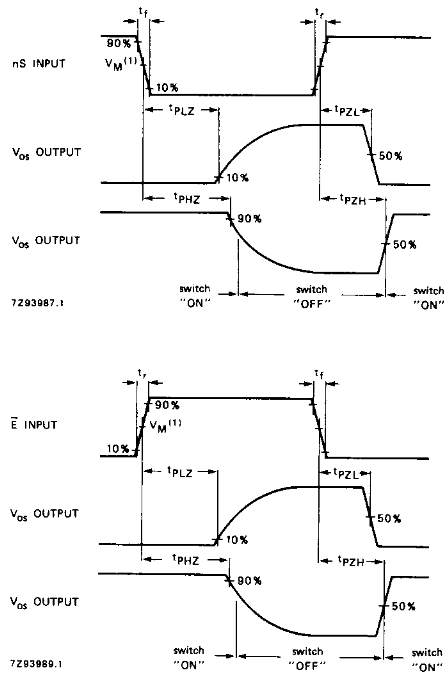


Fig. 19 Waveforms showing the turn-ON and turn-OFF times.

Notes to Fig. 19

(1) HC : V_M = 50%; V_I = GND to V_{CC}.
HCT: V_M = 1.3 V; V_I = GND to 3 V.

TEST CIRCUIT AND WAVEFORMS

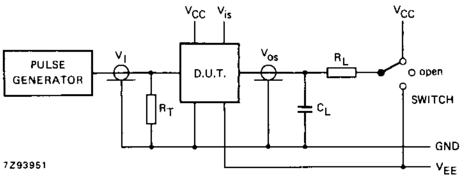


Fig. 20 Test circuit for measuring AC performance.

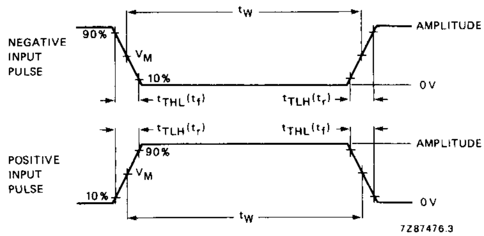


Fig. 21 Input pulse definitions.

Conditions

TEST	SWITCH	V_{is}
t_{PZH}	V_{EE}	V_{CC}
t_{PZL}	V_{CC}	V_{EE}
t_{PHZ}	V_{EE}	V_{CC}
t_{PLZ}	V_{CC}	V_{EE}
others	open	pulse

FAMILY	AMPLITUDE	V_M	t_r; t_f	
			f_{max}; PULSE WIDTH	OTHER
74HC	V_{CC}	50%	< 2 ns	6 ns
74HCT	3.0 V	1.3 V	< 2 ns	6 ns

Definitions for Figs 20 and 21:

C_L = load capacitance including jig and probe capacitance (see AC CHARACTERISTICS for values).

R_T = termination resistance should be equal to the output impedance Z_O of the pulse generator.

t_r = t_f = 6 ns; when measuring f_{max}, there is no constraint on t_r, t_f with 50% duty factor.